

## N-channel 600 V, 0.14 $\Omega$ typ., 20 A MDmesh™ M2 Power MOSFETs in TO-220FP and I<sup>2</sup>PAKFP packages

Datasheet - production data

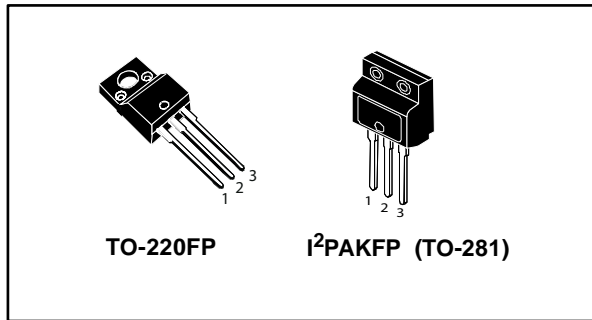
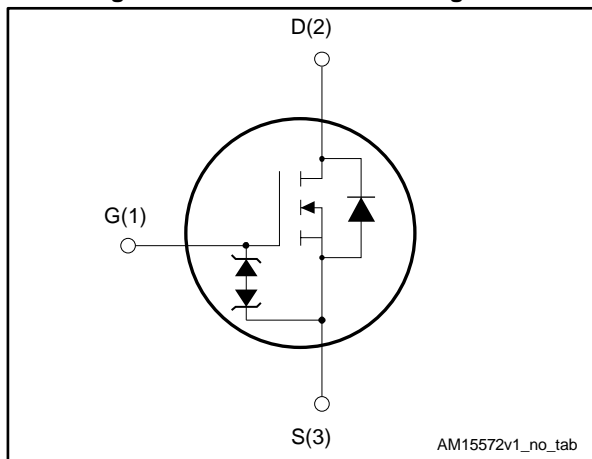


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub> @ T <sub>Jmax</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STF26N60M2	650 V	0.165 $\Omega$	20 A	30 W
STF126N60M2				

- Extremely low gate charge
- Excellent output capacitance (C<sub>OSS</sub>) profile
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications
- LCC converters, resonant converters

### Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STF26N60M2	26N60M2	TO-220FP	Tube
STF126N60M2		I <sup>2</sup> PAKFP	

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$	20	A
	Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$	13	
$I_{DM}^{(2)}$	Drain current (pulsed)	80	A
$P_{TOT}$	Total dissipation at $T_{case} = 25\text{ }^\circ\text{C}$	30	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ ; $T_C = 25\text{ }^\circ\text{C}$ )	2.5	kV
$T_{stg}$	Storage temperature	-55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature		

**Notes:**

- (1) Limited by maximum junction temperature.  
 (2) Pulse width is limited by safe operating area.  
 (3)  $I_{SD} \leq 20\text{ A}$ ,  $di/dt=400\text{ A}/\mu\text{s}$ ;  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$ .  
 (4)  $V_{DS} \leq 480\text{ V}$ .

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	4.2	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	3.8	A
$E_{AR}^{(2)}$	Single pulse avalanche energy	250	mJ

**Notes:**

- (1) Pulse width limited by  $T_{jmax}$ .  
 (2) starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{ V}$ .

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ °C}$  unless otherwise specified)

**Table 5: Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$ , $I_{\text{D}} = 1\text{ mA}$	600			V
$I_{\text{DSS}}$	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$ , $V_{\text{DS}} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{\text{GS}} = 0\text{ V}$ , $V_{\text{DS}} = 600\text{ V}$ , $T_{\text{case}} = 125\text{ °C}$			100	
$I_{\text{GSS}}$	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$ , $V_{\text{GS}} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_{\text{D}} = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$ , $I_{\text{D}} = 10\text{ A}$		0.14	0.165	$\Omega$

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{\text{iss}}$	Input capacitance	$V_{\text{DS}} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{\text{GS}} = 0\text{ V}$	-	1360	-	$\text{pF}$
$C_{\text{oss}}$	Output capacitance		-	88	-	
$C_{\text{rss}}$	Reverse transfer capacitance		-	2	-	
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$ , $V_{\text{GS}} = 0\text{ V}$	-	124	-	$\text{pF}$
$R_{\text{G}}$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_{\text{D}} = 0\text{ A}$	-	4	-	$\Omega$
$Q_{\text{g}}$	Total gate charge	$V_{\text{DD}} = 480\text{ V}$ , $I_{\text{D}} = 20\text{ A}$ , $V_{\text{GS}} = 10\text{ V}$ (see <a href="#">Figure 15</a> : "Gate charge test circuit")	-	34	-	$\text{nC}$
$Q_{\text{gs}}$	Gate-source charge		-	5.6	-	
$Q_{\text{gd}}$	Gate-drain charge		-	16.3	-	

**Notes:**

<sup>(1)</sup>  $C_{\text{oss eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{\text{oss}}$  when  $V_{\text{DS}}$  increases from 0 to 80%  $V_{\text{DSS}}$ .

**Table 7: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$ , $I_{\text{D}} = 10\text{ A}$ $R_{\text{G}} = 4.7\text{ }\Omega$ , $V_{\text{GS}} = 10\text{ V}$ (see <a href="#">Figure 14</a> : "Switching times test circuit for resistive load" and <a href="#">Figure 19</a> : "Switching time waveform")	-	20.2	-	$\text{ns}$
$t_{\text{r}}$	Rise time		-	8	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	66	-	
$t_{\text{f}}$	Fall time		-	10	-	

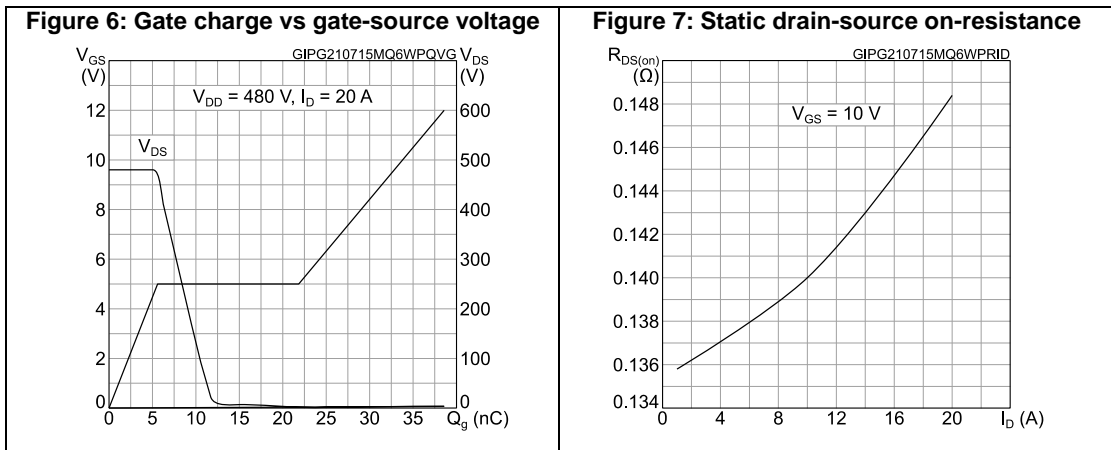
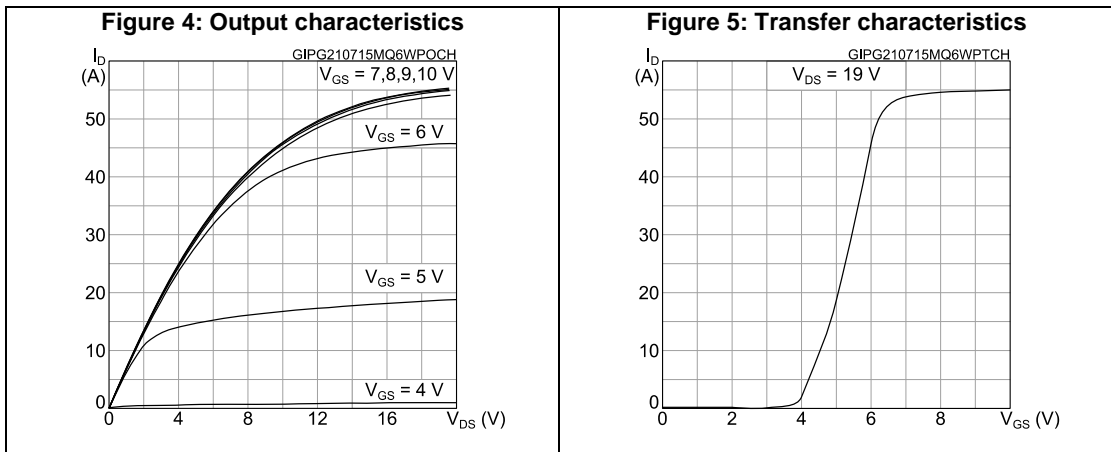
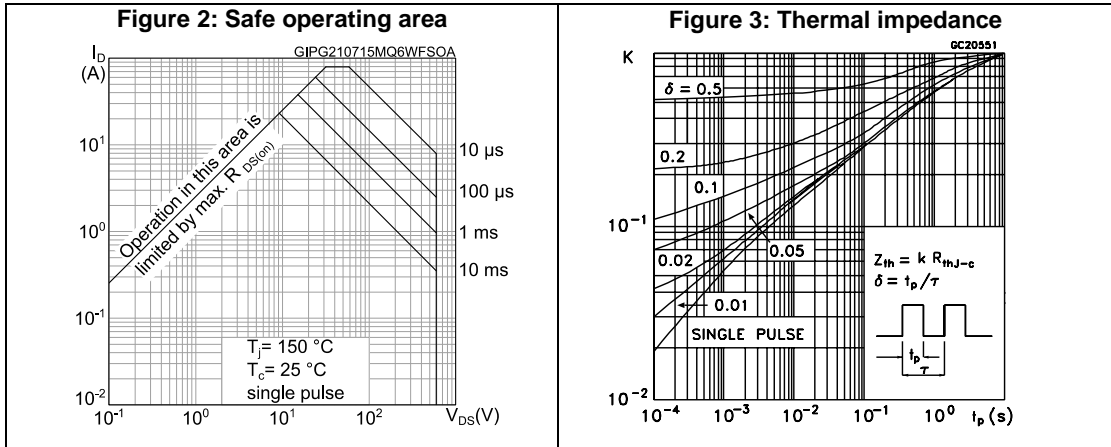
Table 8: Source-drain diode

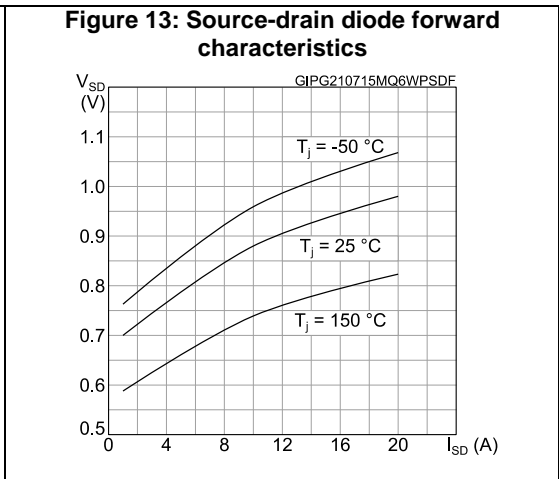
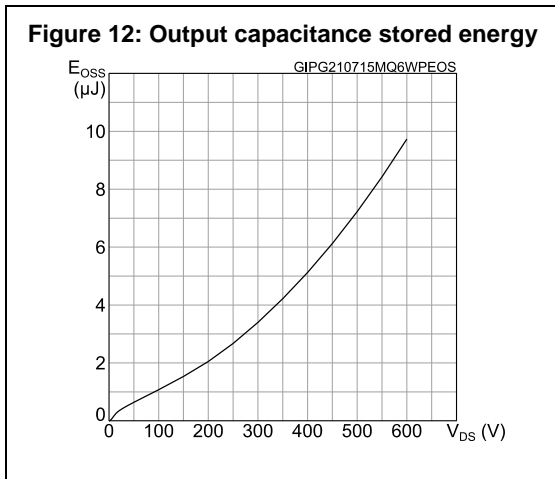
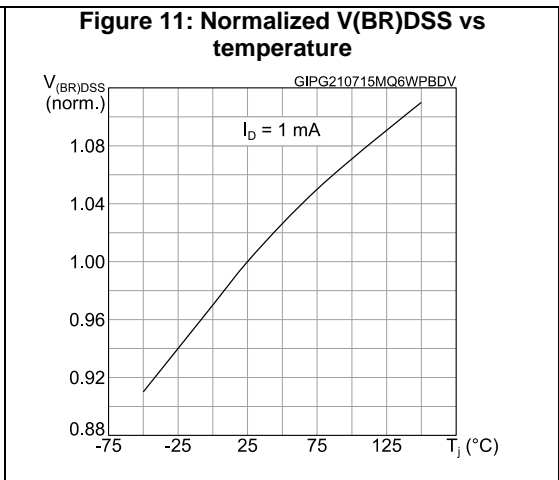
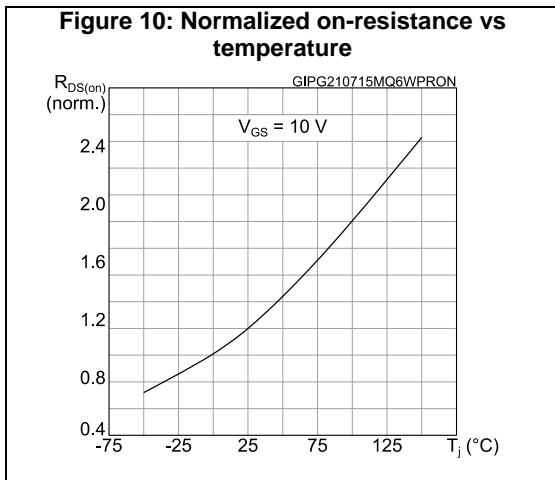
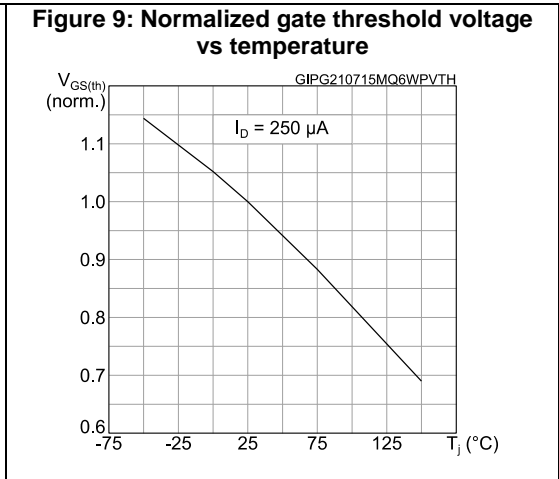
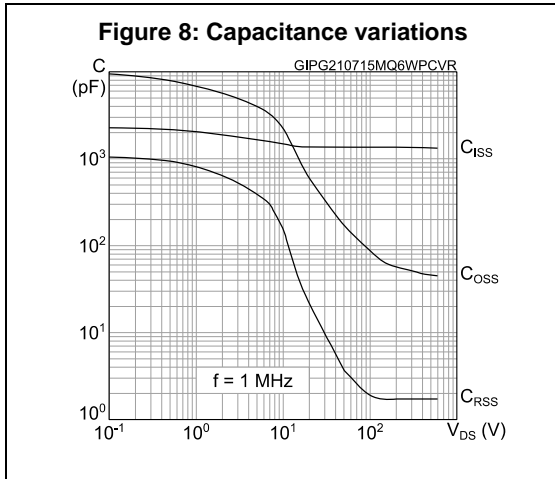
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		20	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 20\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 16</a> : "Test circuit for inductive load switching and diode recovery times")	-	360		ns
$Q_{rr}$	Reverse recovery charge		-	5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	27		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 16</a> : "Test circuit for inductive load switching and diode recovery times")	-	556		ns
$Q_{rr}$	Reverse recovery charge		-	8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	29		A

**Notes:**

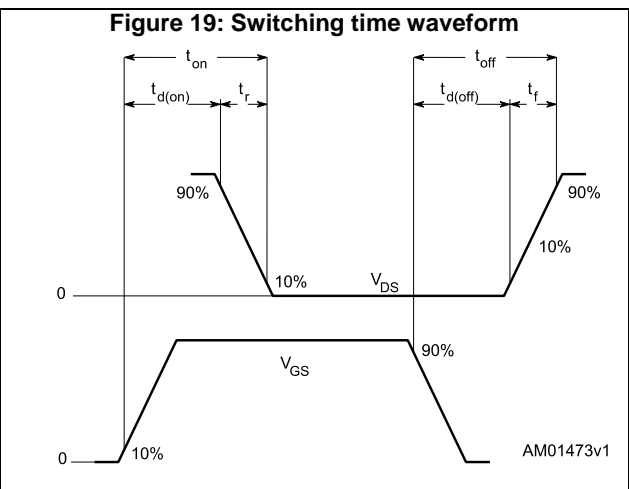
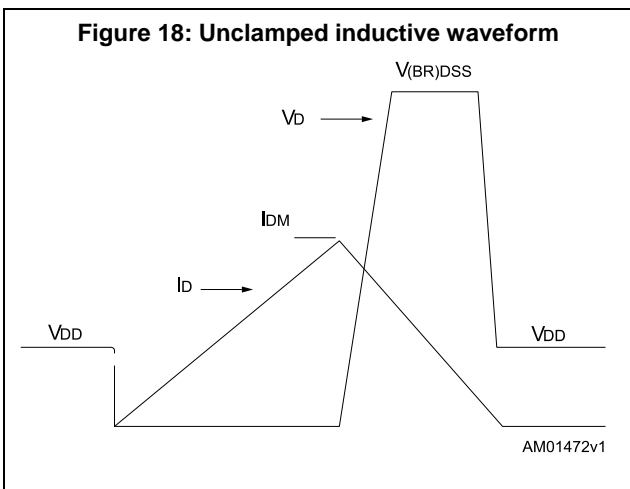
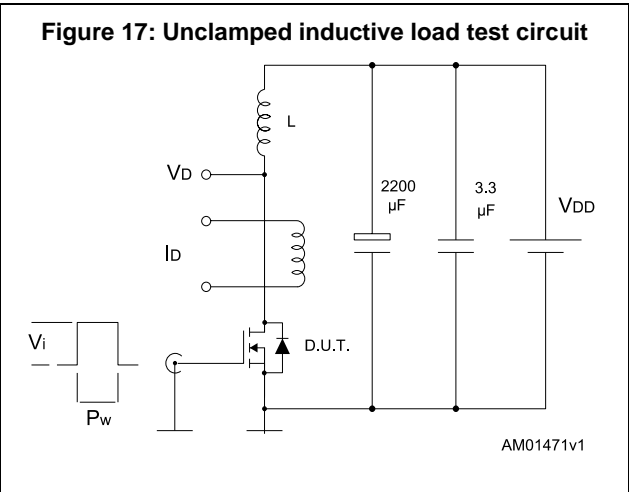
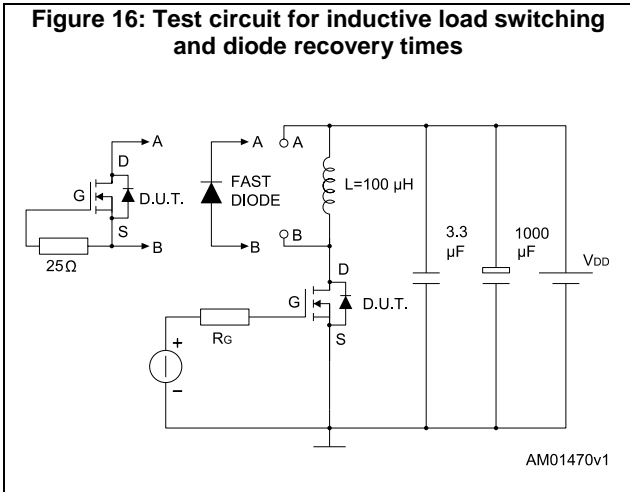
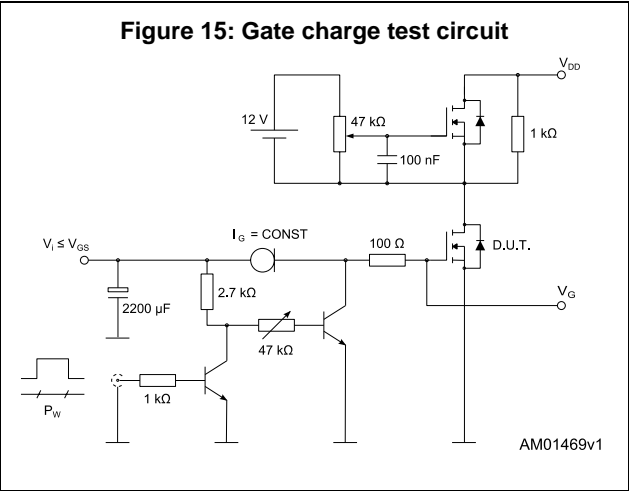
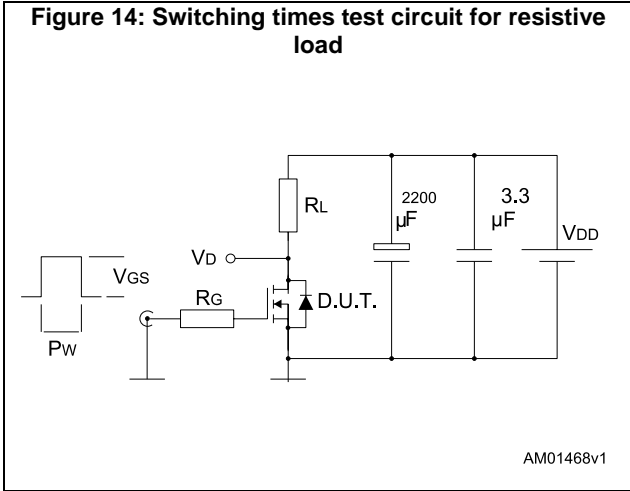
- (1) Pulse width is limited by safe operating area.  
(2) Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)





### 3 Test circuits



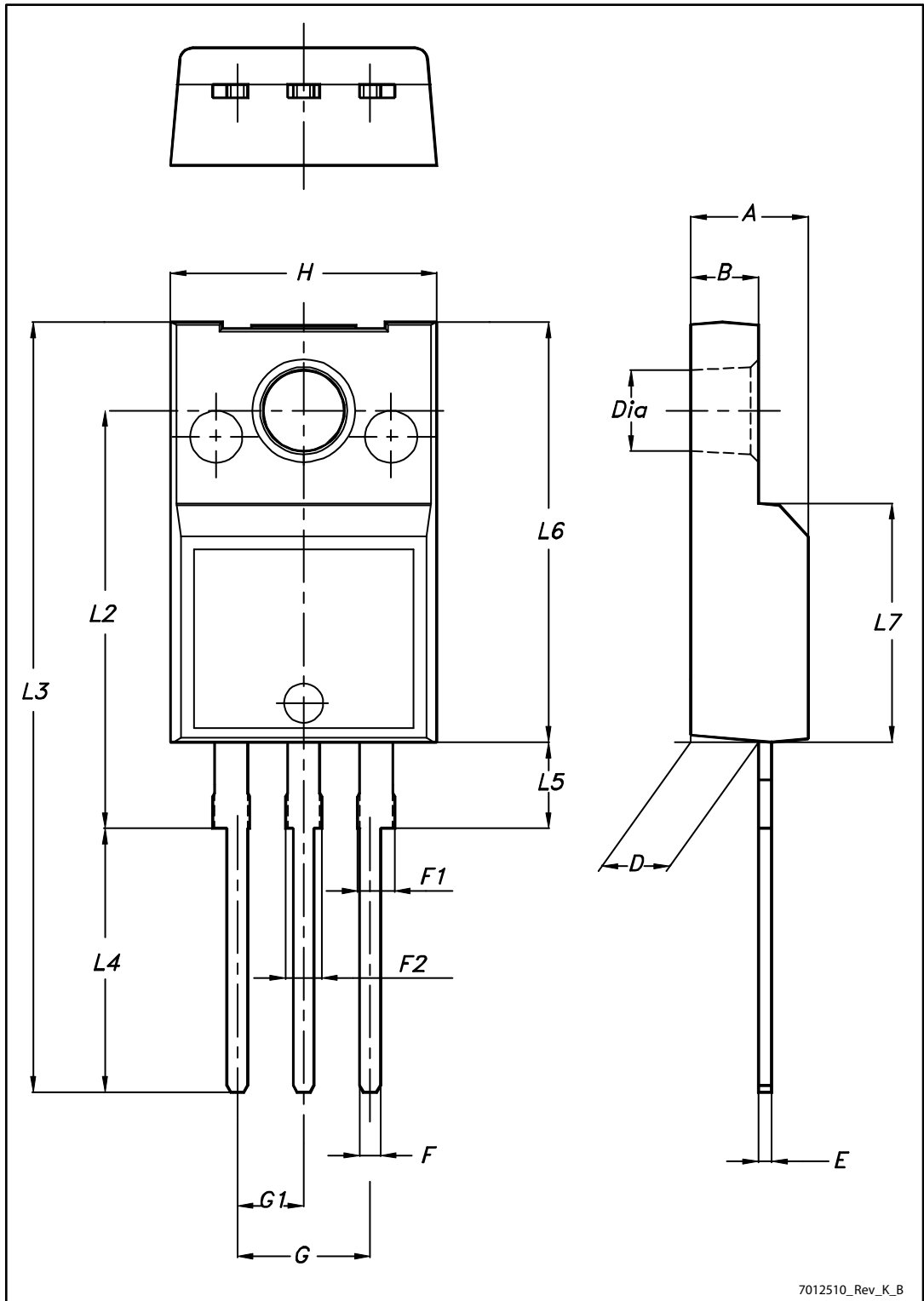


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 TO-220FP package information

Figure 20: TO-220FP package outline



7012510\_Rev\_K\_B

Table 9: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

### 4.2 I<sup>2</sup>PAKFP (TO-281) package information

Figure 21: I<sup>2</sup>PAKFP (TO-281) package outline

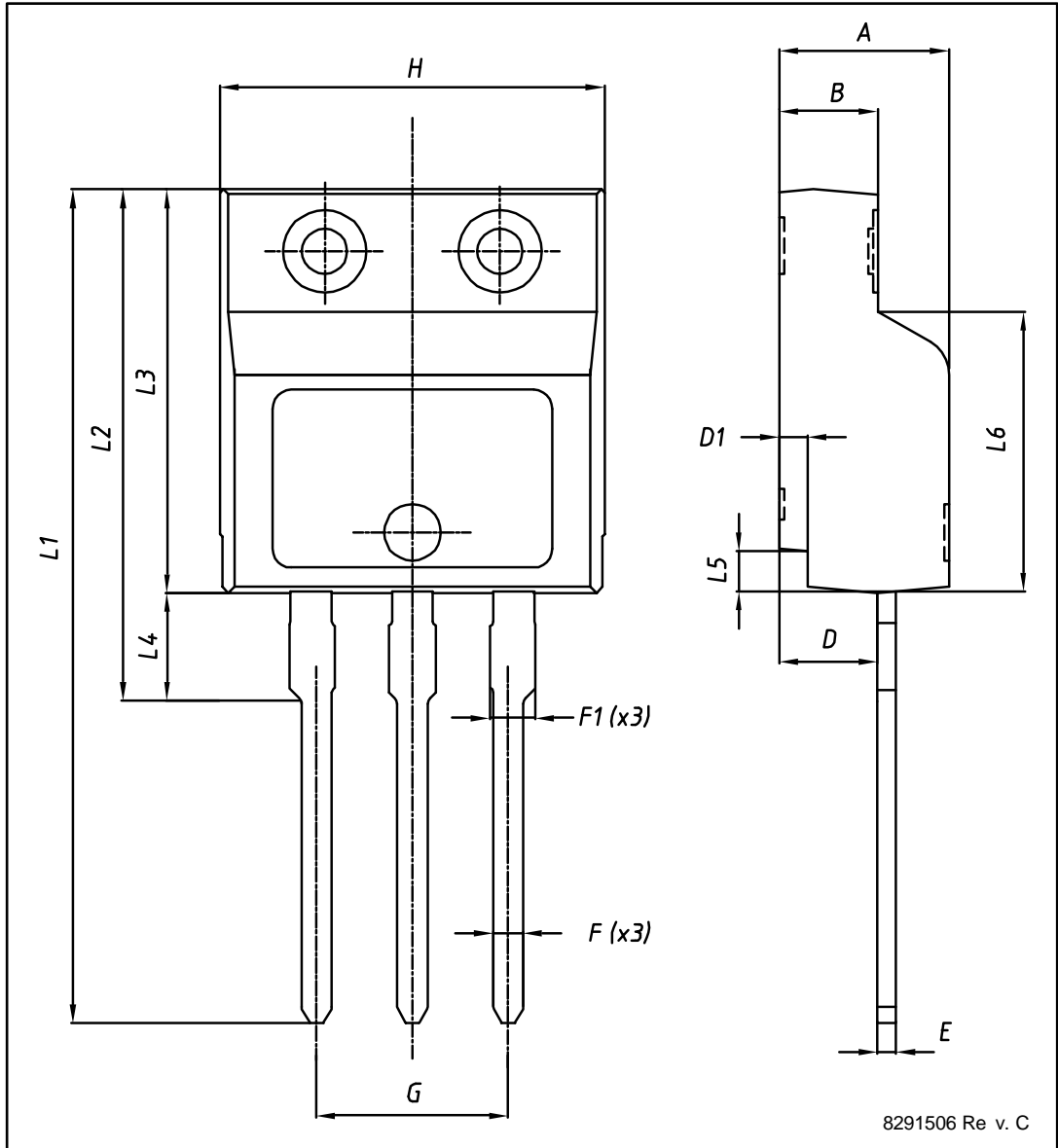


Table 10: I<sup>2</sup>PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40	-	4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95		5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.50	7.60	7.70

## 5 Revision history

Table 11: Document revision history

Date	Revision	Changes
05-Mar-2015	1	First release.
30-July-2015	2	Text and formatting changes throughout document Datasheet promoted from preliminary data to production data In Section <i>Electrical characteristics</i> : - updated and renamed table <i>Static</i> (was On/off states) - updated table <i>Dynamic</i> , <i>Switching times</i> and <i>Source-drain diode</i> - added section <i>Electrical characteristics (curves)</i>

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